Review of: "The electron in the atom, in addition to rotating around it under the influence of the gravitational force of the nucleus, also has a rotational movement around itself"

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Potential competing interests: No potential competing interests to declare.

Obtaining one-dimensional nanoarrays has been mentioned; among them are methods based on lithography (electron beam lithography, optical lithography, electric lithography, ion beam lithography, lithography by scanning microscopes), the vapor phase deposition method (physical vapor deposition and chemical vapor deposition), and methods based on the use of templates. The electron in the atom, in addition to rotating around it under the influence of the gravitational force of the nucleus, also has a rotational movement around itself. This type of rotation in the structure of nanowires is called electron nanospin.

The advantages of using nanoporous aluminum oxide as a template for the production of nanowires compared to other methods include high porosity order, porosity alignment, a controllable length-to-diameter ratio, and high porosity density. The order and dimensions of the nanowires produced using this set of templates are determined and controlled by the initial conditions of the anodizing process. Due to their chemical stability, high saturation magnetization, high axial anisotropy, high binding temperature, excellent chemical stability and corrosion resistance, and high specific nanoelectrical resistance

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